

# **CAT524**

## Configured Digitally Programmable Potentiometer (DPP™): Programmable Voltage Applications

#### **FEATURES**

- Four 8-bit DPPs configured as programmable voltage sources in DAC-like applications
- **■** Common reference inputs
- **■** Buffered wiper outputs
- Non-volatile NVRAM memory wiper storage
- Output voltage range includes both supply rails
- 4 independently addressable buffered output wipers
- 1 LSB accuracy, high resolution
- Serial µP interface
- Single supply operation: 2.7V-5.5V
- Setting read-back without effecting outputs

#### **APPLICATIONS**

- Automated product calibration
- Remote control adjustment of equipment
- Offset, gain and zero adjustments in self-calibrating and adaptive control systems
- Tamper-proof calibrations
- DAC (with memory) substitute

#### **DESCRIPTION**

The CAT524 is a quad, 8-bit digitally-programmable potentiometer (DPP™) configured for programmable voltage and DAC-like applications. Intended for final calibration of products such as camcorders, fax machines and cellular telephones on automated high volume production lines, it is also well suited for self-calibrating systems and for applications where equipment which requires periodic adjustment is either difficult to access or in a hazardous environment.

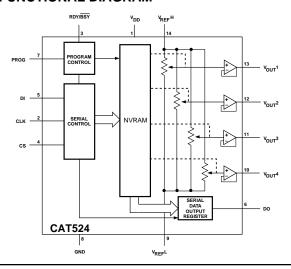
The four independently programmable DPPs have an output range which includes both supply rails. The wipers are buffered by rail to rail op amps. Wiper settings, stored in non-volatile NVRAM memory, are not lost when the device is powered down and are automatically reinstated when power is returned. Each wiper can be dithered to test new output values without effecting

the stored settings, and stored settings can be read back without disturbing the DPP's output.

The CAT524 is controlled with a simple 3 wire serial interface. A Chip Select pin allows several devices to share a common serial interface. Communication back to the host controller is via a single serial data line thanks to the Tri-Stated CAT524 Data Output pin. A RDY/BSY output working in concert with an internal low voltage detector signals proper operation of the non-volatile NVRAM memory Erase/Write cycle.

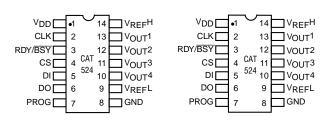
The CAT524 is available in the 0 to  $70^{\circ}$  C commercial and  $-40^{\circ}$  C to  $85^{\circ}$  C industrial operating temperature ranges. Both 14-pin plastic DIP and SOIC packages are offered.

#### **FUNCTIONAL DIAGRAM**



#### PIN CONFIGURATION

DIP Package (P)



SOIC Package (J)

#### **ABSOLUTE MAXIMUM RATINGS\***

Supply Voltage
V <sub>DD</sub> to GND0.5V to +7V
Inputs
CLK to GND0.5V to V <sub>DD</sub> +0.5V
CS to GND0.5V to V <sub>DD</sub> +0.5V
DI to GND0.5V to V <sub>DD</sub> +0.5V
PROG to GND0.5V to V <sub>DD</sub> +0.5V
$V_{REF}H$ to GND0.5V to $V_{DD}$ +0.5V
$V_{REF}L$ to GND0.5V to $V_{DD}$ +0.5V
Outputs
D <sub>0</sub> to GND0.5V to V <sub>DD</sub> +0.5V
V <sub>OUT</sub> 1– 4 to GND–0.5V to V <sub>DD</sub> +0.5V
Operating Ambient Temperature
Commercial ('C' or Blank suffix) 0°C to +70°C
Industrial ('1' suffix) – 40°C to +85°C

Junction Temperature	+150°C
Storage Temperature	–65°C to +150°C
Lead Soldering (10 sec max)	+300°C

<sup>\*</sup>Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. Absolute Maximum Ratings are limited values applied individually while other parameters are within specified operating conditions, and functional operation at any of these conditions is NOT implied. Device performance and reliability may be impaired by exposure to absolute rating conditions for extended periods of time.

### **RELIABILITY CHARACTERISTICS**

Symbol	Parameter	Min	Max	Units	Test Method
V <sub>ZAP</sub> <sup>(1)</sup>	ESD Susceptibility	2000		Volts	MIL-STD-883, Test Method 3015
I <sub>LTH</sub> <sup>(1)(2)</sup>	Latch-Up	100		mA	JEDEC Standard 17

NOTES: 1. This parameter is tested initially and after a design or process change that affects the parameter.

### **DC ELECTRICAL CHARACTERISTICS:**

 $V_{DD}$  = +2.7 to +5.5V,  $V_{REF}H$  =  $V_{DD}$ ,  $V_{REF}L$  = 0V, unless otherwise specified

Symbol	Parameter	Conditions		Min	Тур	Max	Units
	Resolution			8	_	_	Bits
Accuracy		·					
INL	Integral Linearity Error	I <sub>LOAD</sub> = 10 μA	T <sub>R</sub> = C	_	_	± 1	LSB
		$I_{LOAD} = 10 \mu A$	$T_R = I$	_	_	± 1	LSB
		$I_{LOAD} = 40 \mu A$	T <sub>R</sub> = C	_	_	± 2	LSB
		$I_{LOAD} = 40 \mu A$	$T_R = I$	_	_	± 2	LSB
DNL	Differential Linearity Error	$I_{LOAD} = 10 \mu A$	$T_R = C$	_	_	± 0.5	LSB
		$I_{LOAD} = 10 \mu A$	$T_R = I$	_	_	± 0.5	LSB
		$I_{LOAD} = 40 \mu A$	$T_R = C$	_	_	± 1.5	LSB
		$I_{LOAD} = 40 \mu A$	$T_R = I$	_	_	± 1.5	LSB

## **Logic Inputs**

I <sub>IH</sub>	Input Leakage Current	$V_{IN} = V_{DD}$	_	<u> </u>	10	μΑ
I <sub>IL</sub>	Input Leakage Current	$V_{IN} = 0V$	_	_	-10	μΑ
V <sub>IH</sub>	High Level Input Voltage		2	_	$V_{DD}$	V
V <sub>IL</sub>	Low Level Input Voltage		0	_	0.8	V

$V_{RH}$	V <sub>REF</sub> H Input Voltage Range	2.7	_	$V_{DD}$	V
$V_{RL}$	V <sub>REF</sub> L Input Voltage Range	GND	_	V <sub>DD</sub> -2.7	V
Z <sub>IN</sub>	V <sub>REF</sub> H–V <sub>REF</sub> L Resistance	_	7	_	kΩ

V <sub>OH</sub>	High Level Output Voltage	I <sub>OH</sub> = - 40 μA	V <sub>DD</sub> -0.3	_	_	V
V <sub>OL</sub>	Low Level Output Voltage	$I_{OL} = 1 \text{ mA}, V_{DD} = +5V$	_	_	0.4	V
		$I_{OL} = 0.4 \text{ mA}, V_{DD} = +3V$	_	_	0.4	V

<sup>2.</sup> Latch-up protection is provided for stresses up to 100mA on address and data pins from -1V to V<sub>CC</sub> + 1V.

## DC ELECTRICAL CHARACTERISTICS (Cont.):

 $V_{DD} = +2.7V$  to +5.5V ,  $V_{REF}H = +V_{DD}$ ,  $V_{REF}L = 0V$ , unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Analog O	utput					
FSO	Full-Scale Output Voltage	$V_R = V_{REF}H - V_{REF}L$	0.99 V <sub>R</sub>	0.995 V <sub>R</sub>	_	V
ZSO	Zero-Scale Output Voltage	$V_R = V_{REF}H-V_{REF}L$	_	0.005 V <sub>R</sub>	0.01 V <sub>R</sub>	V
IL	DAC Output Load Current		_	_	1	μΑ
R <sub>OUT</sub>	DAC Output Impedance	V <sub>DD</sub> = +5V	_	_	100	kΩ
		V <sub>DD</sub> = +3V	_	_	150	kΩ
PSSR	Power Supply Rejection	I <sub>LOAD</sub> = 250 nA	_	_	1	LSB / V
Temperat	ure					
TCo	V <sub>OUT</sub> Temperature Coefficient	$V_{REF}H = +5V, V_{REF}L = 0V$	_	_	200	μV/ °C
		$V_{DD} = +5V, I_{LOAD} = 250nA$				
TC <sub>REF</sub>	Temperature Coefficient of	V <sub>REF</sub> H to V <sub>REF</sub> L	_	700	_	ppm / °C
	V <sub>REF</sub> Resistance					
Power Su	pply					
I <sub>DD1</sub>	Supply Current (Read)	Normal Operating	_	400	600	μΑ
I <sub>DD2</sub>	Supply Current (Write)	V <sub>DD</sub> =5V	_	1600	2500	μA
		V <sub>DD</sub> =3V	_	1000	1600	μΑ
$V_{DD}$	Operating Voltage Range		2.7	_	5.5	V

## **AC ELECTRICAL CHARACTERISTICS:**

 $V_{DD}$  = +2.7V to +5.5V,  $V_{REF}H$  = + $V_{DD}$ ,  $V_{REF}L$  = 0V, unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Digital				I	I	
t <sub>CSMIN</sub>	Minimum CS Low Time		150	_	_	ns
t <sub>CSS</sub>	CS Setup Time		100	_	_	ns
t <sub>CSH</sub>	CS Hold Time		0	_	_	ns
t <sub>DIS</sub>	DI Setup Time	C <sub>L</sub> = 100 pF,	50	_	_	ns
t <sub>DIH</sub>	DI Hold Time	see note 1	50	_	_	ns
t <sub>DO1</sub>	Output Delay to 1	_	_	_	150	ns
t <sub>DO0</sub>	Output Delay to 0	_	_	_	150	ns
t <sub>HZ</sub>	Output Delay to High-Z		_	400	_	ns
t <sub>Busy</sub>	Erase/Write Cycle Time		_	4	5	ms
t <sub>LZ</sub>	Output Delay to Low-Z		_	400	_	ns
t <sub>PROG</sub>	Erase/Write Pulse Width		700	_	_	ns
t <sub>PS</sub>	PROG Setup Time		150	_	_	ns
t <sub>CLK</sub> H	Minimum CLK High Time		500	_	_	ns
t <sub>CLK</sub> L	Minimum CLK Low Time		300	_	_	ns
f <sub>C</sub>	Clock Frequency		DC	_	1	MHz
Analog						
t <sub>DS</sub>	DAC Settling Time to 1/2 LSB	$C_{LOAD} = 10 \text{ pF}, V_{DD} = +5V$	_	3	10	μs
		$C_{LOAD} = 10 \text{ pF}, V_{DD} = +3V$	_	6	10	μs
Pin Capa	citance				1	
C <sub>IN</sub>	Input Capacitance	$V_{IN} = 0V, f = 1 \text{ MHz}^{(2)}$	_	8	_	pF
C <sub>OUT</sub>	Output Capacitance	$V_{OUT} = 0V, f = 1 \text{ MHz}^{(2)}$	_	6	_	pF

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**NOTES:** 1. All timing measurements are defined at the point of signal crossing  $V_{DD}$  / 2.

2. These parameters are periodically sampled and are not 100% tested.

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## A. C. TIMING DIAGRAM

PARAM LIMING NAME FROM TO	tCLKH Rising CLK edge to falling CLK edge	tCLKL Falling CLK edge to CLK rising edge	tcsH Falling CLK edge for last data bit (DI) to falling CS edge	S Rising CS edge to next rising CLK edge		tCSMIN Falling CS edge to rising CS edge	Data valid to first rising CLK edge after CS = high	Rising CLK edge to end of data valid	Rising CLK edge to D0 = low	Rising CS edge to D0 becoming high low impedance (active output)	Rising CLK edge to D0 = high	Falling CS edge to D0 becoming high impedance (Tri-State)	Rising PROG edge to next rising CLK edge	Rising PROG edge to falling PROG edge	Falling CLK edge after PROG=H to rising RDY/BSY edge	
PARAM						<u> </u>		Rising	Rising C	Rising CS ow imped	Rising CL	-alling CS mpedance	Rising PR	Rising PR	<sup>-</sup> alling CLI ising RDY	
	_		ပ္	tcss		tCSMIN	tois [	t <sub>DIH</sub>	t DO0	trz	tD01	t HZ	tps	tPROG F	tBUSY F	
t o 1	+ tolkH ↑			↑ tcss → tclkl ↑ ↑ ↑ tclkl ↑ ↑ · · · · · · · · · · · · · · · · ·	SS	tCSMIN ★		<b>↓</b> HQ1		→ t <sub>Z</sub> → 1	Q	- too₁ <del> </del>	PROG		RDY/BSY	

#### PIN DESCRIPTION

Pin	Name	Function
1	$V_{DD}$	Power supply positive.
2	CLK	Clock input pin.Clock input pin.
3	RDY/BSY	Ready/Busy Output
4	CS	Chip Select
5	DI	Serial data input pin.
6	DO	Serial data output pin.
7	PROG	EEPROM Programming Enable
		Input
8	GND	Power supply ground.
9	$V_{REF}L$	Minimum DAC output voltage.
10	V <sub>OUT</sub> 4	DAC output channel 4.
11	V <sub>OUT</sub> 3	DAC output channel 3.
12	V <sub>OUT</sub> 2	DAC output channel 2.
13	V <sub>OUT</sub> 1	DAC output channel 1.
14	$V_{REF}H$	Maximum DAC output voltage.

#### DAC addressing is as follows:

DAC OUTPUT	Α0	<b>A</b> 1
V <sub>OUT</sub> 1	0	0
V <sub>OUT</sub> 2	1	0
V <sub>OUT</sub> 3	0	1
V <sub>OUT</sub> 4	1	1

#### **DEVICE OPERATION**

The CAT524 is a quad 8-bit Digital to Analog Converter (DAC) whose outputs can be programmed to any one of 256 individual voltage steps. Once programmed, these output settings are retained in non-volatile EEPROM memory and will not be lost when power is removed from the chip. Upon power up the DACs return to the settings stored in EEPROM memory. Each DAC can be written to and read from independently without effecting the output voltage during the read or write cycle. Each output can also be temporarily adjusted without changing the stored output setting, which is useful for testing new output settings before storing them in memory.

#### **DIGITAL INTERFACE**

The CAT524 employs a standard 3 wire serial control interface consisting of Clock (CLK), Chip Select (CS) and Data In (DI) inputs. For all operations, address and data are shifted in LSB first. In addition, all digital data must be preceded by a logic "1" as a start bit. The DAC address and data are clocked into the DI pin on the clock's rising edge. When sending multiple blocks of information a minimum of two clock cycles is required between the last block sent and the next start bit.

Multiple devices may share a common input data line by selectively activating the CS control of the desired IC. Data Outputs (DO) can also share a common line because the DO pin is Tri-Stated and returns to a high impedance when not in use.

#### **CHIP SELECT**

Chip Select (CS) enables and disables the CAT524's read and write operations. When CS is high data may be

read to or from the chip, and the Data Output (DO) pin is active. Data loaded into the DAC control registers will remain in effect until CS goes low. Bringing CS to a logic low returns all DAC outputs to the settings stored in EEPROM memory and switches DO to its high impedance Tri-State mode.

Because CS functions like a reset the CS pin has been equipped with a 30 ns to 90 ns filter circuit to prevent noise spikes from causing unwanted resets and the loss of volatile data.

#### **CLOCK**

The CAT524's clock controls both data flow in and out of the IC and EEPROM memory cell programming. Serial data is shifted into the DI pin and out of the DO pin on the clock's rising edge. While it is not necessary for the clock to be running between data transfers, the clock must be operating in order to write to EEPROM memory, even though the data being saved may already be resident in the DAC control register.

No clock is necessary upon system power-up. The CAT524's internal power-on reset circuitry loads data from EEPROM to the DACs without using the external clock.

As data transfers are edge triggered clean clock transitions are necessary to avoid falsely clocking data into the control registers. Standard CMOS and TTL logic families work well in this regard and it is recommended that any mechanical switches used for breadboarding or device evaluation purposes be debounced by a flip-flop or other suitable debouncing circuit.

### **VREF**

 $V_{REF}$ , the voltage applied between pins  $V_{REF}$ Hand $V_{REF}$ L, sets the DAC's Zero to Full Scale output range where  $V_{REF}$ L = Zero and  $V_{REF}$ H = Full Scale.  $V_{REF}$  can span the full power supply range or just a fraction of it. In typical applications  $V_{REF}$ H and  $V_{REF}$ L are connected across the power supply rails. When using less than the full supply voltage  $V_{REF}$ H is restricted to voltages between  $V_{DD}$  and  $V_{DD}/2$  and  $V_{REF}$ L to voltages between GND and  $V_{DD}/2$ .

## READY/BUSY

When saving data to non-volatile EEPROM memory, the Ready/Busy ouput (RDY/BSY) signals the start and duration of the EEPROM erase/write cycle. Upon receiving a command to store data (PROG goes high) RDY/BSY goes low and remains low until the programming cycle is complete. During this time the CAT524 will ignore any data appearing at DI and no data will be output on DO.

RDY/ $\overline{BSY}$  is internally ANDed with a low voltage detector circuit monitoring V<sub>DD</sub>. If V<sub>DD</sub> is below the minimum value required for EEPROM programming, RDY/ $\overline{BSY}$  will remain high following the program command indicating a failure to record the desired data in non-volatile memory.

#### **DATA OUTPUT**

Data is output serially by the CAT524, LSB first, via the Data Out (DO) pin following the reception of a start bit and two address bits by the Data Input (DI). DO becomes active whenever CS goes high and resumes its high impedance Tri-State mode when CS returns low. Tri-Stating the DO pin allows several 524s to share a single serial data line and simplifies interfacing multiple 524s to a microprocessor.

#### WRITING TO MEMORY

Programming the CAT524's EEPROM memory is ac-

complished through the control signals: Chip Select (CS) and Program (PROG). With CS high, a start bit followed by a two bit DAC address and eight data bits are clocked into the DAC control register via the DI pin. Data enters on the clock's rising edge. The DAC output changes to its new setting on the clock cycle following D7, the last data bit.

Programming is achieved by bringing PROG high for a minimum of 3 ms. PROG must be brought high sometime after the start bit and at least 150 ns prior to the rising edge of the clock cycle immediately following the D7 bit. Two clock cycles after the D7 bit the DAC control register will be ready to receive the next set of address and data bits. The clock must be kept running throughout the programming cycle. Internal control circuitry takes care of ramping the programming voltage for data transfer to the EEPROM cells. The CAT524 EEPROM memory cells will endure over 100,000 write cycles and will retain data for a minimum of 20 years without being refreshed.

#### **READING DATA**

Each time data is transferred into a DAC control register currently held data is shifted out via the D0 pin, thus in every data transaction a read cycle occurs. Note, however, that the reading process is destructive. Data must be removed from the register in order to be read. Figure 2 depicts a Read Only cycle in which no change occurs in the DAC's output. This feature allows  $\mu$ Ps to poll DACs for their current setting without disturbing the output voltage but it assumes that the setting being read is also stored in EEPROM so that it can be restored at the end of the read cycle. In Figure 2 CS returns low before the 13<sup>th</sup> clock cycle completes. In doing so the EEPROM's setting is reloaded into the DAC control register. Since



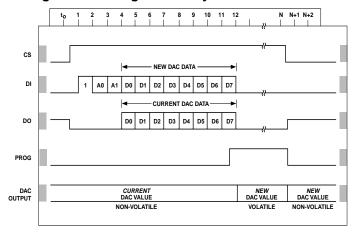
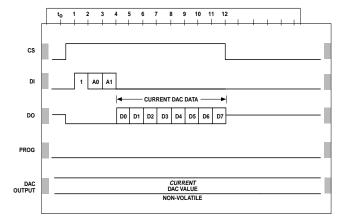


Figure 2. Reading from Memory



this value is the same as that which had been there previously no change in the DAC's output is noticed. Had the value held in the control register been different from that stored in EEPROM then a change would occur at the read cycle's conclusion.

#### **TEMPORARILY CHANGE OUTPUT**

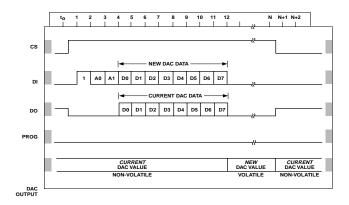
The CAT524 allows temporary changes in DAC's output to be made without disturbing the settings retained in EEPROM memory. This feature is particularly useful when testing for a new output setting and allows for user adjustment of preset or default values without losing the original factory settings.

Figure 3 shows the control and data signals needed to effect a temporary output change. DAC settings may be changed as many times as required and can be made to any of the four DACs in any order or sequence. The temporary setting(s) remain in effect long as CS remains high. When CS returns low all four DACs will return to the output values stored in EEPROM memory.

When it is desired to save a new setting acquired using

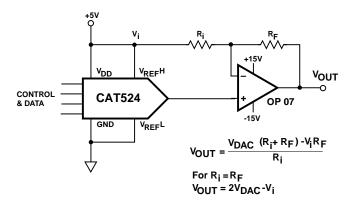
this feature, the new value must be reloaded into the DAC control register prior to programming. This is because the CAT524's internal control circuitry discards the new data from the programming register two clock cycles after receiving it (after reception is complete) if no PROG signal is received.

Figure 3. Temporary Change in Output

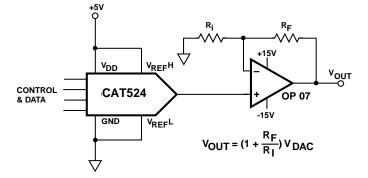


#### **APPLICATION CIRCUITS**

DAC	INPUT	DAC OUTPUT	ANALOG OUTPUT
		$V_{DAC} = \frac{CODE}{255} (V_{FS} - V_{ZERO}) + V_{ZERO}$ $V_{FS} = 0.99 V_{RFF}$	
мѕв	LSB	V <sub>ZERO</sub> = 0.01 V <sub>REF</sub>	V <sub>REF</sub> = 5V R <sub>I</sub> = R <sub>F</sub>
1111	1111	$\frac{255}{255}$ (.98 V <sub>REF</sub> ) + .01 V <sub>REF</sub> = .990 V <sub>REF</sub>	V <sub>OUT</sub> = +4.90V
1000	0000	128 (.98 V <sub>REF</sub> ) + .01 V <sub>REF</sub> = .502 V <sub>REF</sub>	V <sub>OUT</sub> = +0.02V
0111	1111	$\frac{127}{255}$ (.98 V <sub>REF</sub> ) + .01 V <sub>REF</sub> = .498 V <sub>REF</sub>	V <sub>OUT</sub> = -0.02V
0000	0001	$\frac{1}{255}$ (.98 V <sub>REF</sub> ) + .01 V <sub>REF</sub> = .014 V <sub>REF</sub>	V <sub>OUT</sub> = -4.86V
0000	0000	$\frac{0}{255}$ (.98 V <sub>REF</sub> ) + .01 V <sub>REF</sub> = .010 V <sub>REF</sub>	V <sub>OUT</sub> = -4.90V



#### **Bipolar DPP Output**

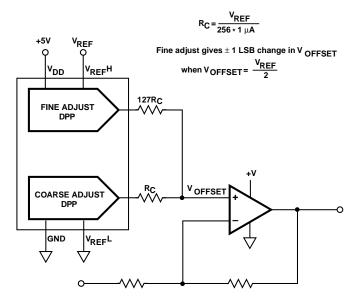


**Amplified DPP Output** 

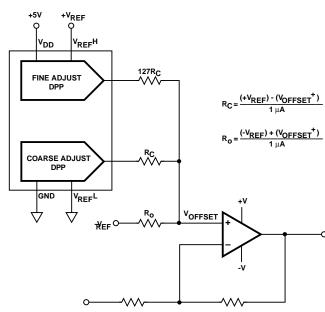
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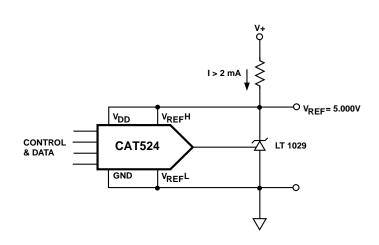
## **APPLICATION CIRCUITS (Cont.)**



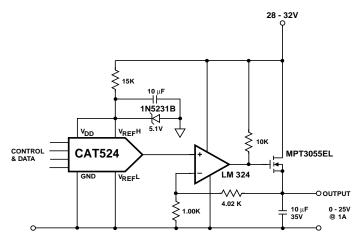
Coarse-Fine Offset Control by Averaging DPP Outputs for Single Power Supply Systems



Coarse-Fine Offset Control by Averaging DPP Outputs for Dual Power Supply Systems

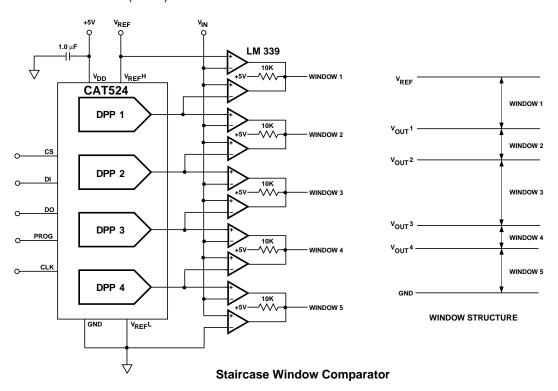


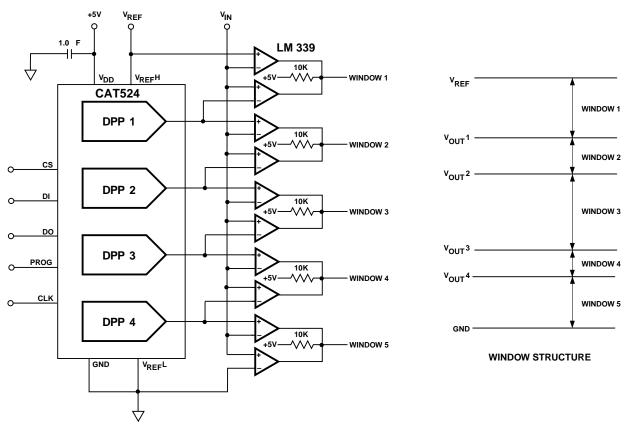
**Digitally Trimmed Voltage Reference** 



**Digitally Controlled Voltage Reference** 

## **APPLICATION CIRCUITS (Cont.)**

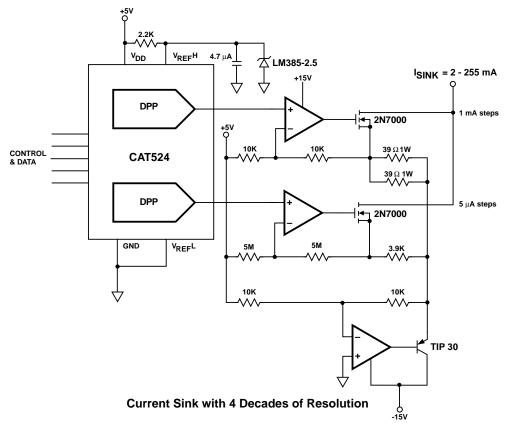


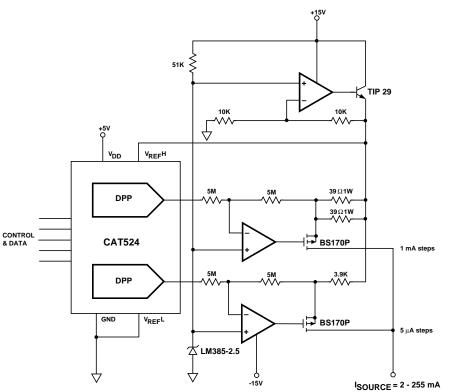


**Overlapping Window Comparator** 

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## **APPLICATION CIRCUITS (Cont.)**





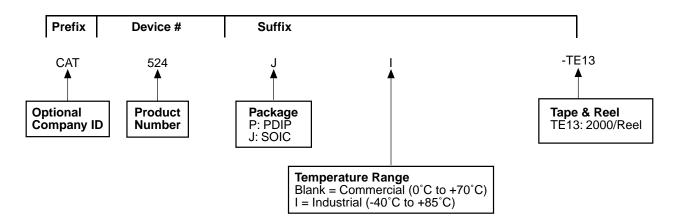
**Current Source with 4 Decades of Resolution** 

#### **APPLICATION CIRCUITS (Cont.)** 1N914 뉯 10K √√∧ **1.0** μF 74C14 **-005** μF 1N914 💆 VCC = **0.1** μF **0.01** μF **2.5** μ**F** TREB CAP **0.47** μF INPUT 1 O-IN 1 BASS CAP ₩ $\textbf{0.39}~\mu\text{F}$ 20V IN5250B 19 ٧z OUTPUT 1 -O OUT 1 $V_{DD}$ **CAT524** LM1040 1.0 μF VREFH LOUDNESS cs CHIP SELECT. O-47K PROG VOLUME PROGRAM O-V<sub>OUT</sub>1 DI BALANCE DATA IN O-Vou<sub>T</sub>2 10 μF DO TREBLE BYPASS DATA OUT O-V<sub>OUT</sub> 3 | <mark>10 μ</mark>Ε 10 CLK CLOCK O-VouT4 BASS 0.22 0.22 0.22 μF μF VREFL -O OUT 2 OUTPUT 2 GND **0.47** μF **0.39** μF INPUT 2 O-IN 2 BASS CAP TREB CAP STEREO **0.01** μF GND ENHANCE 4.7K GND

**Digital Stereo Control** 

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## **ORDERING INFORMATION**



#### Notes:

(1) The device used in the above example is a CAT524JI-TE13 (SOIC, Industrial Temperature, Tape & Reel)